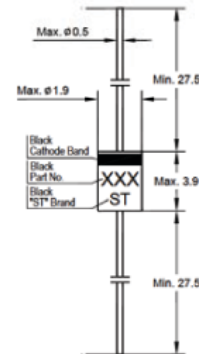


Silicon Epitaxial Planar Switching Diode

for general purpose switching applications

Features

- Fast switching speed
- High reliability



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---|-------------|-------------------|------------------|
| Non-Repetitive Peak Reverse Voltage | V_{RM} | 50 | V |
| Forward Continuous Current | I_{FM} | 300 | mA |
| Average Rectified Forward Current | $I_{F(AV)}$ | 200 | mA |
| Power Dissipation | P_{tot} | 500 ¹⁾ | mW |
| Junction Temperature | T_j | 200 | $^\circ\text{C}$ |
| Operating and Storage Temperature Range | T_{stg} | - 65 to + 175 | $^\circ\text{C}$ |

¹⁾Valid provided that leads are at a distance of 8 mm from case kept at ambient temperature

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|---|----------|------|------|
| Forward Voltage at $I_F = 200\text{ mA}$ | V_F | 1.2 | V |
| Reverse Current at $V_R = 50\text{ V}$ | I_R | 100 | nA |
| Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\ \Omega$ | t_{rr} | 4 | ns |